

Average gate power dissipation ($T_j=125$)	$P_{G(AV)}$	0.1	W
Peak gate power	P_{GM}	2	W
Peak pulse voltage ($T_j=25$; non-repetitive, off-state; FIG.8)	V_{pp}	2.5	kV

($T_j=25$ unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	$V_D=12V R_L=33$	-	MAX.	10	mA
V_{GT}		-	MAX.	1.3	V
V_{GD}	$V_D=V_{DRM} T_j=125$ $R_L=3.3K$	-	MIN.	0.15	V
I_L	$I_G=1.2I_{GT}$		MAX.	40	mA
				20	
I_H	$I_T=100mA$		MAX.	20	mA
dV/dt	$V_D=540V$ Gate Open $T_j=125$		MIN.	1000	V/ μs
(dI/dt) _c	(dV/dt) _c =15V/ μs , $T_j=125$		MIN.	2	A/ms
t_{on}	$I_G=20mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	2.5	μs
t_{off}				25	
V_{CL}	$I_{CL}=0.1mA t_p=1ms$		MIN.	950	V

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	$I_{TM}=1.1A t_p=380\mu s$	$T_j=25$	1.35	V
V_{TO}	Threshold voltage	$T_j=125$	0.8	V
R_D	Dynamic resistance	$T_j=125$	385	m
I_{DRM}	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	2	mA
I_{RRM}		$T_j=125$	0.2	mA

Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	25	$^{\circ}W$
$R_{th(j-a)}$	junction to ambient (AC)	150	$^{\circ}W$

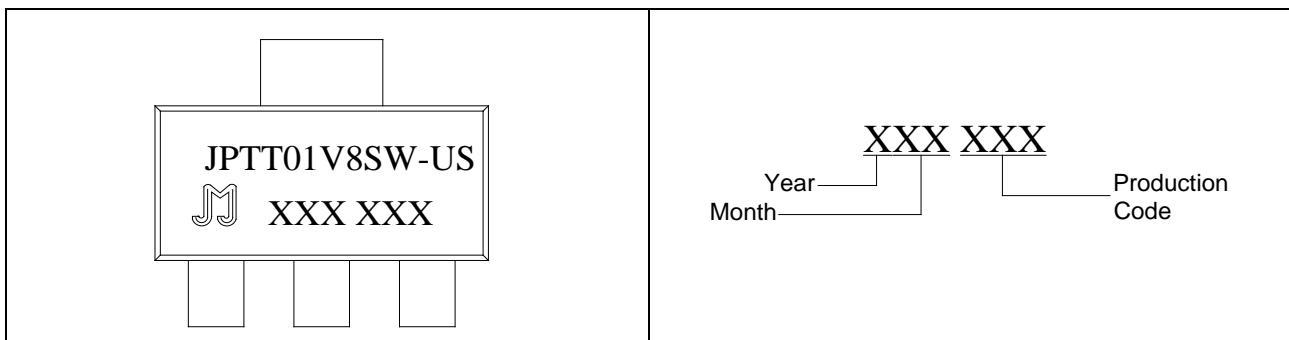
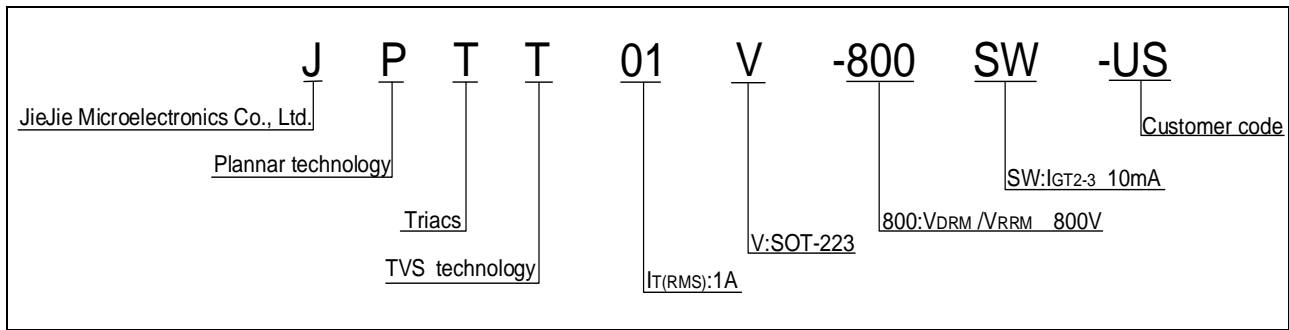
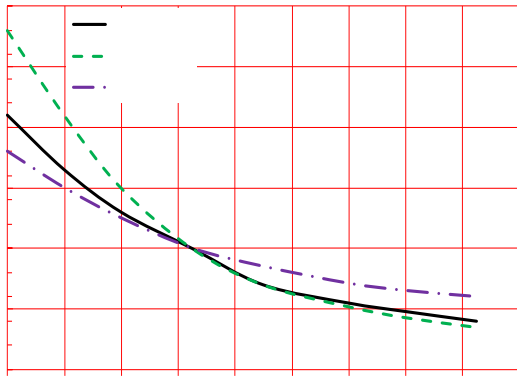


FIG.1 Maximum power dissipation versus RMS on-state current

FIG.2: RMS on-state current versus case temperature

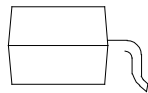
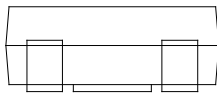
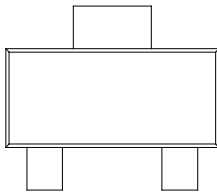
FIG.7: Relative variations of gate trigger current, holding current and latching current versus junction temperature



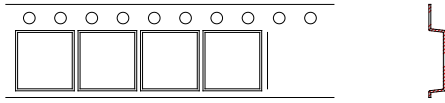
Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JPTT01V-800SW-US	800	10	SOT-223	4,000	Tape & Reel

Document Revision History

Date	Revision	Changes
May.15, 2023	A-1	Last updated




Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	1.5	1.6	1.8	0.059	0.063	0.071
A1	0.01	0.06	0.10	0.001	0.002	0.004
B	2.9	3.0	3.1	0.114	0.118	0.122
B1	0.6	0.7	0.8	0.024	0.028	0.031
C	0.22	0.26	0.32	0.009	0.010	0.013
D	6.3	6.5	6.7	0.248	0.256	0.264
E	3.3	3.5	3.7	0.130	0.138	0.146
F	4.4			0.173		
F1	2.2			0.087		
G	0.5		1.0	0.020		0.039
H	1.5	1.75	2.0	0.059	0.069	0.079
J	6.7	7.0	7.3	0.264	0.276	0.287
K		0.9			0.035	



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	-		12.30	-		0.482
E	1.65	1.75	1.85	0.065	0.069	0.073
F	5.45	5.50	5.55	0.215	0.217	0.219
D0		1.55	1.60		0.061	0.063
D1		-	-			
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.95	2.00	2.05	0.077	0.079	0.081
10P0	39.80	40.00	40.20	1.567	1.575	1.583
A0	6.85	6.95	7.05	0.269	0.273	0.276
B0	7.15	7.25	7.35	0.280	0.284	0.288
K0	1.95	2.05	2.15	0.076	0.080	0.084
T	0.20	0.25	0.30	0.008	0.010	0.012

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